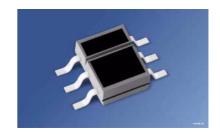
Reflexlichtschranke mit VCSEL-Sender Reflective Interrupter with VCSEL-Emitter

SFH 9221



Wesentliche Merkmale

- Großer Arbeitsabstand (2-10mm)
- IR-GaAs-VCSEL (Vertical Cavity Surface Emitting Laser)in Kombination mit einer Si-Fotodiode
- · Enge Strahlverteilung des Senders
- Tageslichtsperrfilter

Anwendungen

- Positionssensor
- Endabschaltung
- Drehzahlüberwachung, -regelung
- Bewegungssensor
- Strichcodeleser

Features

- Long operating distance (2-10mm)
- IR-GaAs-VCSEL (Vertical Cavity Surface Emitting Laser) in combination with a Silicon photodiode
- Narrow beam characteristics of the emitter
- Daylight cut-off filter

Applications

- · Position sensor
- End position switch
- · Speed monitoring and regulating
- Motion sensor
- · Bar Code reading

Typ	Bestellnummer	$I_{\rm P}$ [µA]	(see note on page 5)
Type	Ordering Code	($I_{\rm F}$ = 8 mA, $V_{\rm R}$ = 5 V, d = 5 mm)	
SFH 9221	Q62702-P5468	1 <	

Beim Betrieb dieses Bauteils sind die Sicherheitsvorschriften für die Laserklasse 1M nach IEC 60825-1 Am. 2 zu beachten.

Operating this device the safety instructions for laser class 1M according to IEC 60825-1 Am. 2 have to be observed.



ATTENTION - Observe Precautions For Handling - Electrostatic Sensitive Device

2004-08-30



Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit	
Sender (GaAs-VCSEL-Diode) Emitter (GaAs VCSEL diode)				
Sperrspannung Reverse voltage	V_{R}	3	V	
Vorwärtsgleichstrom Forward current	I_{F}	10	mA	
Verlustleistung Power dissipation	P_{tot}	25	mW	
Empfänger (Si-Fotodiode) Detector (silicon photodiode) Sperrspannung	V_{R}	20	V	
Reverse Voltage	V _R	20	V	
Verlustleistung Total power dissipation	P_{tot}	150	mW	
Reflexlichtschranke Reflective Interrupter				
Lagertemperatur Storage temperature range	$T_{ m stg}$	- 40 + 85	°C	
Betriebstemperatur Operating temperature range	T_{op}	- 40 + 85	°C	
Elektrostatische Entladung Electrostatic discharge	ESD	400	V	
Umweltbedingungen / Environment conditions	3 K3 acc. to E	3 K3 acc. to EN 60721-3-3 (IEC 721-3-3)		



Kennwerte ($T_A = 25$ °	'C)
Characteristics	

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Sender (GaAs-VCSEL Diode) Emitter (GaAs-VCSEL diode)			
Wellenlänge der Strahlung Wavelength at peak emission $I_{\rm F}=8~{\rm mA},t_{\rm p}=20~{\rm ms}$	λ_{peak}	850	nm
Spektrale Bandbreite bei 50% von $I_{\rm max}$ Spectral bandwidth at 50% of $I_{\rm max}$ $I_{\rm F}$ = 8 mA	Δλ	1	nm
Abstrahlwinkel Half angle $I_{\rm F}$ = 10 mA	φ	± 15	Grad deg.
Schwellenstrom ¹⁾ Threshold current ¹⁾	$I_{ m th}$	2.6 (<5)	mA
Durchlaβspannung Forward voltage $I_{\rm F}$ = 10 mA	V_{F}	1.8 (≤ 2.3)	V
	I_{R}	0.01 (≤ 1)	μΑ
Kapazität Capacitance $V_{\rm R}$ = 0 V, f = 1 MHz	Co	25	pF
Wärmewiderstand ²⁾ Thermal resistance ²⁾	R_{thJA}	1500	K/W
Empfänger (Si-Fotodiode) Detector (silicon photodiode)			
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	λ _{S max}	900	nm
Dunkelstrom, $V_{\rm R}$ = 10 V Dark current	I_{R}	50 (≤ 5000)	pA
Kapazität, $V_{\rm R}$ = 0 V, f = 1 MHz, E = 0 Capacitance	C_0	13	pF



Kennwerte ($T_A = 25$ °C) Characteristics (cont'd)

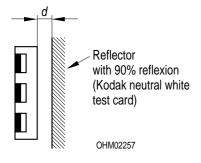
Bezeichnung	Symbol	Wert	Einheit
Parameter	Symbol	Value	Unit

Reflexlichtschranke Reflective Interrupter

Fotostrom	$I_{P\;min.}$	1	μΑ
Photocurrent			
Kodak neutral white test card, 90% Reflexion			
$I_{\rm F}$ = 8 mA; $V_{\rm R}$ = 5 V; d = 5 mm			
(see note on page 5)			

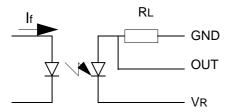
 $^{^{\}rm 1)}~$ Der VCSEL emittiert nur bei Flussströmen größer als $I_{\rm th}$

- ²⁾ Montage auf PC-Board mit > 5 mm² Padgröβe
- 2) Mounting on pcb with > 5 mm² pad size



 $^{^{\}rm 1)}~$ VCSEL only emits at forward currents higher than $I_{\rm th}$

Schaltzeiten ($T_{\rm A}$ = 25 °C, $V_{\rm R}$ = 5 V, $I_{\rm P}$ = 1.5 $\mu{\rm A}^{1)}$, $R_{\rm L}$ = 50 Ω) Switching Times



Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Anstiegzeit Rise time	t_{r}	10	ns
Abfallzeit Fall time	t_{f}	10	ns

¹⁾ I_P eingestellt über den Durchlaβstrom der Sendediode, den Reflexionsgrad und den Abstand des Reflektors vom Bauteil (d)

Anm.: Es wird empfohlen die Lichtschranke bei dem spezifizierten Arbeitpunkt von ca. 8mA für den Emitter einzusetzten, weil andere Betriebsströme zu einem größeren Streubereich beim Koppelfaktor führen. Der Abgleich erfolgt über den Arbeitswiderstand am Detektor.

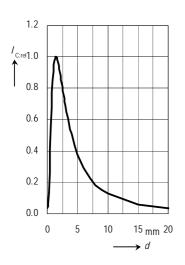
Von einem Einsatz der Lichtschranke mit glänzenden oder gar spiegelnden Oberflächen wird abgeraten. Die Abstrahlcharakteristik des Senders ändert sich sowohl über die Temperatur als auch mit dem Flußstrom stärker als bei Standardemittern und führt somit ebenfalls zur Erhöhung des Streubereichs beim Koppelfaktor. Bei diffuser Streuung ist dieser Einfluß jedoch gering, und kann für die meisten Anwendungen vernachlässigt werden.

Note: It is recomended to use the interrupter at the specified emitter current of about 8mA, as other operating currents lead to a larger coupling factor variation. The tuning is done using the operating resistor on the detector side. It is not recomended to use the interrupter in combination with shiny or mirror like surfaces. Changes in temperatures and operating current are having a bigger influence on the radiation characteristic as it is the case for standard emitters. This means a higher variance of the coupling factor. For diffuse surfaces the mentioned influence is low, and can be neglected for most of the applications.

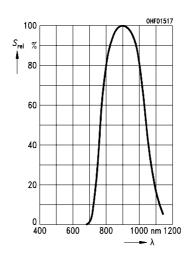


 $I_{\rm P}$ as a function of the forward current of the emitting diode, the degree of reflection and the distance between reflector and component (d)

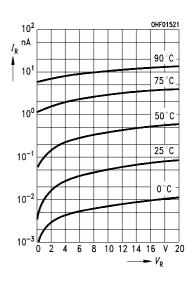
$\begin{array}{l} \textbf{Photocurrent} \ \ \frac{I_{\rm p}}{I_{\rm pmax}} = \textit{f(d)} \\ \textbf{Kodak 90\%} \end{array}$



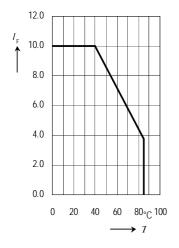
Relative Spectral Sensitivity



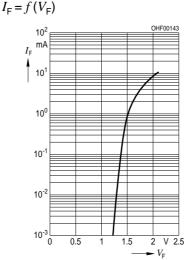
Dark Current



Max. Permissible Forward Current $I_{\rm F} = f\left(T_{\rm A}\right)$

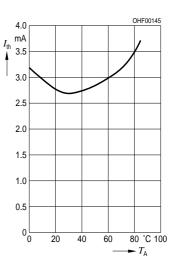


Forward Current



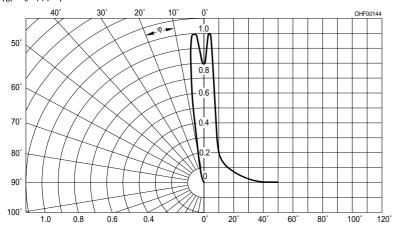
6

Threshold Current $I_{th} = f(T_A)$



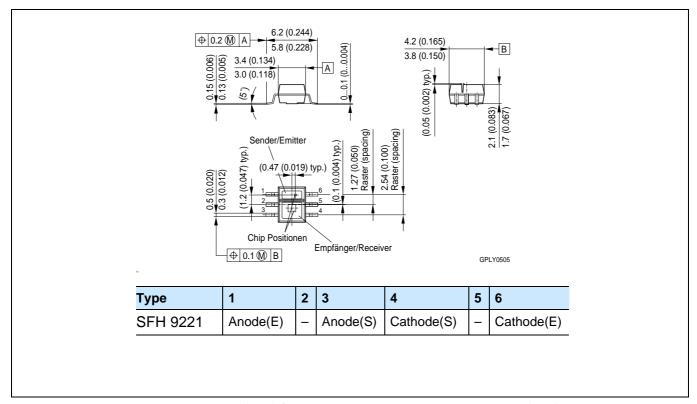
Target Radiation characteristics

$$I_{rel} = f(\varphi) I_F = 10 \text{mA}$$



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Maßzeichnung Package Outlines

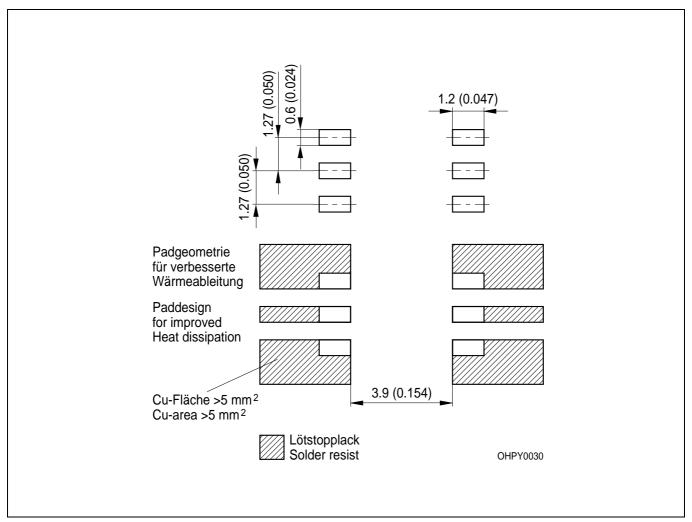


Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).



Empfohlenes Lötpaddesign Recommended Solder Pad

IR-Reflow Löten IR REflow Soldering



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

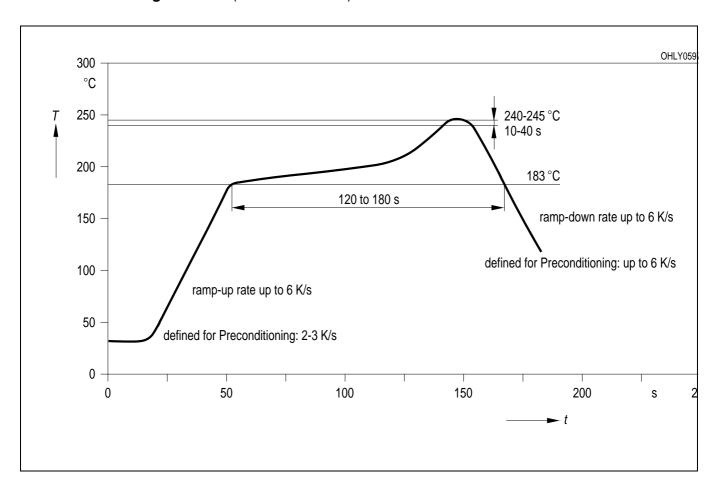


Löthinweise Soldering Conditions

Bauform Drypack Type Level acc.			Tauch-, Schwalllötung Dip, Wave Soldering		Reflowlötung Reflow Soldering	
	to IPS-stand. 020	Peak Temp. (solderbath)	Max. Time in Peak Zone	Peak Temp. (package temp.)	Max. Time in Peak Zone	(Iron temp.)
SFH 9221	4	n. a.	_	245 °C	10 sec.	n.a.

Bitte Verarbeitungshinweise für SMT-Bauelemente beachten! Please observe the handling guidelines for SMT devices!

IR-Reflow Lötprofil (nach IPC 9501) **IR Reflow Soldering Profile** (acc. to IPC 9501)





Gurtung / Polarität und Lage

siehe Dokument: Short Form Katalog: Gurtung und Verpackung - SMT-Bauelemente - Gehäuse:SMT RLS

Methode of Taping / Polarity and Orientation see document: Short Form Catalog: Tape and Reel - SMT-Components - Package: SMT-RLS

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